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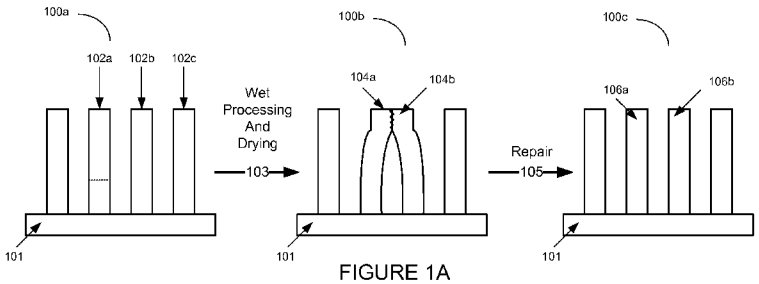


FIGURE 1A

(57) Abstract: A method is provided for processing a wafer used in fabricating semiconductor devices. The method can comprise forming high-aspect ratio features on the wafer, which is followed by wet processing and drying. During drying, pattern collapse can occur. This pattern collapse can be repaired to allow for additional processing of the wafer. In some instance, pattern collapse can be repaired via etching where the etching breaks bonds that can have formed during pattern collapse.

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